John Haig H Marsh

List of Publications by Year
in descending order

303	4,444	156536	198040
papers	citations	32 h-index	52 g-index

305	305	305	1896
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Gold-viral particle identification by deep learning in wide-field photon scattering parametric images. Applied Optics, 2022, 61, 546.	0.9	3
2	EML Based on Identical Epitaxial Layer, Side-Wall Grating and HSQ Planarization. IEEE Photonics Technology Letters, 2022, 34, 317-320.	1.3	3
3	Surface plasmon polaritons excitation at the interface ofÂgraphene and sodium media. European Physical Journal Plus, 2022, 137, 1.	1.2	2
4	Monolithically Integrated AlGaInAs MQW Polarization Mode Converter Using a Stepped Height Ridge Waveguide. IEEE Photonics Journal, 2022, 14, 1-6.	1.0	4
5	Temporal Evolution of Refractive Index Induced by Short Laser Pulses Accounting for Both Photoacoustic and Photothermal Effects. Applied Sciences (Switzerland), 2022, 12, 6256.	1.3	2
6	Characterization of deep sub-wavelength nanowells by imaging the photon state scattering spectra. Optics Express, 2021, 29, 1221.	1.7	5
7	Low Divergence Dual-Grating Distributed Feedback Lasers Operating at 1.0 Î¼m. , 2021, , .		0
8	Quantitative analysis of errors caused by vibration on polarization parametric indirect microscopic imaging system. Applied Optics, 2021, 60, 2141.	0.9	0
9	Monolithic DWDM source with precise channel spacing. Journal of Semiconductors, 2021, 42, 042301.	2.0	2
10	Traveling-Wave Electroabsorption Modulated Laser Based on Identical Epitaxial Layer Scheme and HSQ Planarization. , 2021, , .		1
11	Photon Scattering Signal Amplification in Gold-Viral Particle Ligation Towards Fast Infection Screening. IEEE Photonics Journal, 2021, 13, 1-11.	1.0	6
12	Dual Wavelength Laser Designed for Locking to Cs-133 Atomic Transitions. , 2021, , .		1
13	Polarization multi-parametric imaging method for the inspection of cervix cell. Optics Communications, 2021, 488, 126846.	1.0	6
14	Electroabsorption Modulated Laser Based on Identical Epitaxial Layer and Transmission Line Technology. , 2021, , .		0
15	Label-free sensing of virus-like particles below the sub-diffraction limit by wide-field photon state parametric imaging of a gold nanodot array. Nanoscale Advances, 2021, 3, 6882-6887.	2.2	4
16	Numerical Simulation of Enhanced Photoacoustic Generation and Wavefront Shaping by a Distributed Laser Array. Applied Sciences (Switzerland), 2021, 11, 9497.	1.3	1
17	Design and Optimization of 1.55 Î¼m AlGaInAs MQW Polarization Mode Controllers. Photonics, 2021, 8, 422.	0.9	2
18	Modeling and Measurement of a HSQ Passivated UTC-PD with a 68.9 GHz Bandwidth. , 2021, , .		0

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19	Design of 2 Î¼m Wavelength Polarization Mode Controllers. , 2020, , .		1
20	Microparticle manipulation using laser-induced thermophoresis and thermal convection flow. Scientific Reports, 2020, 10, 19169.	1.6	18
21	High Precision Laser Ranging Based on STM32 Microcontroller. , 2020, , .		2
22	EML Based on Lumped Configuration, Identical Epitaxial Layer and HSQ Planarization. , 2020, , .		2
23	Comparison of Cross-section Profile Designs for Integrated Polarization Mode Controllers. , 2020, , .		0
24	Photonic integrated circuits for terahertz source generation. IET Optoelectronics, 2020, 14, 136-142.	1.8	3
25	Visualization of ultrasonic wave field by stroboscopic polarization selective imaging. Optics Express, 2020, 28, 27096.	1.7	13
26	Frequency comb with 100â€‰â€‰GHz spacing generated by an asymmetric MQW passively mode-locked laser. Optics Letters, 2020, 45, 2760.	1.7	6
27	1-Î¼m distributed feedback laser with low divergence angle. , 2020, , .		0
28	Novel Electroabsorption Modulator Design Based on Coplanar Waveguide Configuration. , 2019, , .		2
29	Thick film hydrogen silsesquioxane planarization for passive component technology associated with electronic-photonic integrated circuits. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2019, 37, .	0.6	4
30	1.55-Î¼m AlGaInAs/InP Sampled Grating Laser Diodes for Mode Locking at Terahertz Frequencies. IEEE Journal of Selected Topics in Quantum Electronics, 2018, 24, 1-8.	1.9	7
31	Mode Locking at THz Repetition Frequencies using Lasers with Phase Shifted Sampled Gratings. , 2018, , .		0
32	Terahertz Signal Generation Based on a Dual-Mode 1.5 Âµm DFB Semiconductor Laser. , 2018, , .		2
33	Generation of THz Radiation by Sampled Grating DBR Mode Locked Laser Diodes. , 2018, , .		1
34	Mode-Locked Laser Diodes and Their Monolithic Integration. IEEE Journal of Selected Topics in Quantum Electronics, 2017, 23, 1-11.	1.9	32
35	Integrated gratings for novel photonic integrated circuits. , 2017, , .		0
36	Integrated phase-locked laser diodes at 1.55Î¼m. , 2017, , .		0

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37	Multiple-wavelength distributed-feedback laser arrays with high coupling coefficients and precise channel spacing. Optics Letters, 2017, 42, 1800.	1.7	13
38	THz repetition frequency mode-locked laser using novel sampled gratings. , 2017, , .		2
39	DFB laser arrays with precise channel separation and high coupling coefficient. , 2017, , .		0
40	Monolithic Multi-Colour 40 GHz Mode-Locked Laser Array. , 2016, , .		1
41	Improvement of indoor VLC network downlink scheduling and resource allocation. Optics Express, 2016, 24, 26838.	1.7	6
42	Phased locked laser diode by using passive array of multi-mode interference couplers. , 2016, , .		1
43	Fully integrated multi-optoelectronic synthesizer for THz pumping source in wireless communications with rich backup redundancy and wide tuning range. Scientific Reports, 2016, 6, 29084.	1.6	10
44	Photonic Integrated Circuits Based on Quantum well Intermixing Techniques. Procedia Engineering, 2016, 140, 107-114.	1.2	10
45	The UK National Quantum Technologies Hub in sensors and metrology (Keynote Paper). Proceedings of SPIE, 2016, , .	0.8	10
46	Integration of mode-locked diode lasers. Proceedings of SPIE, 2016, , .	0.8	0
47	DWDM Source Based on Monolithic Side-Wall Sample Grating DFB Laser Array. , 2016, , .		3
48	Optoelectronic THz Frequency Synthesizer Based on a Multiple Laser Photonic Integrated Circuit. , 2016, , .		0
49	1.55 Î¼m DFB laser monolithically integrated with 3-stage power amplifier array. , 2015, , .		1
50	Generation of High Speed Polarization Modulated Data Using a Monolithically Integrated Device. IEEE Journal of Selected Topics in Quantum Electronics, 2015, 21, 207-211.	1.9	5
51	Ultra-short pulse generation using semiconductor lasers. , 2015, , .		0
52	155-Î¼m distributed feedback laser monolithically integrated with amplifier array. Optics Letters, 2015, 40, 213.	1.7	6
53	High-Power and Low-Noise Mode-Locking Operation of Al-Quaternary Laser Diodes. IEEE Journal of Selected Topics in Quantum Electronics, 2015, 21, 10-16.	1.9	8
54	Laterally coupled dual-grating distributed feedback lasers for generating mode-beat terahertz signals. Optics Letters, 2015, 40, 182.	1.7	25

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55	Laterally-Coupled Dual-Grating Distributed Feedback Lasers for Generating Mode-Beat Terahertz Signals. , 2015, , .		1
56	A High Power and Ultrahigh Frequency Mode-Locked Laser Monolithically Integrated with an SOA. , 2015, , .		0
57	240â€‰GHz pedestal-free colliding-pulse mode-locked laser with a wide operation range. Laser Physics Letters, 2014, 11, 115804.	0.6	11
58	Monolithically Integrated Polarization Mode Convertors with Semiconductor Lasers. , 2014, , .		0
59	Mode-locking and frequency mixing at THz repetition rates in a sampled-grating DBR mode-locked laser. , 2014, , .		0
60	Mode-locking and frequency mixing at THz pulse repetition rates in a sampled-grating DBR mode-locked laser. Optics Express, 2014, 22, 21690.	1.7	6
61	Mode-locked semiconductor lasers: from Giga-Hertz to Tera-Hertz. , 2014, , .		0
62	Merging pedagogical approaches: University of Glasgow-UESTC joint education programme in electronics and electrical engineering. , 2014, , .		0
63	High channel count and high precision channel spacing multi-wavelength laser array for future PICs. Scientific Reports, 2014, 4, 7377.	1.6	95
64	160 GHz Passively Mode-Locked AlGaInAs 1.55 Î¼m Strained Quantum-Well Lasers With Deeply Etched Intracavity Mirrors. IEEE Journal of Selected Topics in Quantum Electronics, 2013, 19, 1100409-1100409.	1.9	13
65	Dynamics of semiconductor passively mode-locked lasers: Experiment and theory. , 2013, , .		2
66	EML Based on Side-Wall Grating and Identical Epitaxial Layer Scheme. IEEE Photonics Technology Letters, 2013, 25, 1169-1172.	1.3	21
67	High-Power AlGaInAs Mode-Locked DBR Laser With Integrated Tapered Optical Amplifier. IEEE Photonics Technology Letters, 2013, 25, 253-256.	1.3	3
68	Monolithic Mode-Locked Laser With an Integrated Optical Amplifier for Low-Noise and High-Power Operation. IEEE Journal of Selected Topics in Quantum Electronics, 2013, 19, 1100808-1100808.	1.9	14
69	Mode locking at terahertz frequencies using a distributed Bragg reflector laser with a sampled grating. Optics Letters, 2013, 38, 1113.	1.7	16
70	Subpicosecond Colliding Pulse Mode Locking at 126 GHz in Monolithic GaAs/AlGaAs Quantum Well Lasers: Experiments and Theory. IEEE Journal of Selected Topics in Quantum Electronics, 2013, 19, 1100608-1100608.	1.9	15
71	Timing and conditions of poly-phase metamorphism within the Twelve Mile Bay shear zone: implications for the evolution of mid-crustal decollement zones and western Grenville tectonics. International Geology Review, 2013, 55, 525-547.	1.1	6
72	Generating Terahertz Pulses Using Mode-Locked Side-Wall Sampled-Grating Distributed Bragg Reflector Lasers. , 2013, , .		0

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73	490 fs pulse generation from a passive C-band AlGaInAs/InP quantum well mode-locked laser. Optics Letters, 2012, 37, 773.	1.7	12
74	Narrow linewidth laterally coupled 155ÂÎ¼m AlGaInAs/InP distributed feedback lasers integrated with a curved tapered semiconductor optical amplifier. Optics Letters, 2012, 37, 4525.	1.7	34
75	High frequency optoelectronic oscillators based on the optical feedback of semiconductor mode-locked laser diodes. Optics Express, 2012, 20, 3268.	1.7	53
76	A semiconductor laser with monolithically integrated dynamic polarization control. Optics Express, 2012, 20, 20545.	1.7	21
77	High power (130ÂmW) 40ÂGHz 155ÂÎ¼m mode-locked distributed Bragg reflector lasers with integrated optical amplifiers. Optics Letters, 2012, 37, 344.	1.7	8
78	Ultralow 192 Hz RF linewidth optoelectronic oscillator based on the optical feedback of mode-locked laser diodes. , 2012, , .		0
79	High average power (200 mW) 40 GHz mode-locked DBR lasers with integrated tapered optical amplifiers. , 2012, , .		2
80	160-GHz 1.55-$mu{m m}$ Colliding-Pulse Mode-Locked AlGaInAs/InP Laser With High Power and Low Divergence Angle. IEEE Photonics Technology Letters, 2012, 24, 1057-1059.	1.3	9
81	AlGaInAs/InP Monolithically Integrated DFB Laser Array. IEEE Journal of Quantum Electronics, 2012, 48, 137-143.	1.0	26
82	Output Power Limitations and Improvements in Passively Mode Locked GaAs/AlGaAs Quantum Well Lasers. IEEE Journal of Quantum Electronics, 2012, 48, 318-327.	1.0	13
83	10 GHz AlGaInAs/InP 155 Î¼m passively mode-locked laser with low divergence angle and timing jitter. Optics Express, 2011, 19, B75.	1.7	15
84	CWDM source based on AlGaInAs/InP monolithically integrated DFB laser array. Optics Letters, 2011, 36, 4188.	1.7	14
85	10-GHz AlGaInAs/InP 1.55-mum Passively Mode-Locked Laser With Low Divergence Angle and Timing Jitter. IEEE Photonics Technology Letters, 2011, 23, 1079-1081.	1.3	7
86	160 GHz 1.55 µm colliding-pulse mode-locked AlGaInAs/InP laser with reduced optical overlap. , 2011, , .		0
87	80-GHz AlGaInAs/InP 1.55 µm colliding-pulse mode-locked laser with low divergence angle and timing jitter. , 2011, , .		0
88	Colliding-pulse mode-locked AlGaInAs laser operating at 20 GHz with narrow RF linewidth. , 2011, , .		0
89	High peak power (550 mW) 40 GHz mode-locked DBR lasers with integrated optical amplifiers. , 2011, , .		0
90	High-Performance Visible Semiconductor Lasers Operating at 630 nm. IEEE Photonics Journal, 2010, 2, 563-570.	1.0	3

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91	Multi-element arrays for LADAR. , 2009, , .		0
92	High-Performance Red Lasers With Low Beam Divergence. IEEE Photonics Journal, 2009, 1, 172-177.	1.0	9
93	High d/gamma values in diode laser structures for very high power. Proceedings of SPIE, 2009, , .	0.8	14
94	High reliability operation of 2 kW QCW 10-bar laser diode stacks at 808 nm. Proceedings of SPIE, 2009, , .	0.8	0
95	Ultra-fine pitch individually addressable visible laser arrays for high speed digital printing applications. , 2009, , .		4
96	Analysis of thermal performance of InGaP/InGaAlP quantum wells for high-power red laser diodes. Optical and Quantum Electronics, 2008, 40, 1149-1154.	1.5	8
97	High reliability, high power arrays of 808 nm single mode diode lasers employing various quantum well structures. Proceedings of SPIE, 2008, , .	0.8	1
98	Graded-bandgap quantum-dot lasers and arrays. , 2008, , .		0
99	253 mW/μm maximum power density from 9xx nm epitaxial laser structures with d/Γ greater than 1 μm. , 2008, , .		5
100	High-power laser arrays with 100% fill factor emission facet. , 2008, , .		0
101	Spectral slicing of femtosecond pulses using semiconductor modulator arrays. Proceedings of SPIE, 2008, , .	0.8	0
102	Laser arrays transform printing. Nature Photonics, 2007, 1, 387-389.	15.6	1
103	Temperature Behaviour of Pulse Repetition Frequency in Passively Mode-Locked InGaAsP/InP Laser Diodeâ€"Experimental Results and Simple Model. IEEE Journal of Selected Topics in Quantum Electronics, 2007, 13, 1209-1214.	1.9	11
104	Broad-area InAsâˆ•GaAs quantum dot lasers incorporating Intermixed passive waveguide. Electronics Letters, 2007, 43, 29.	0.5	6
105	High-power, high-brightness, high-reliability laser diodes emitting at 800-1000 nm. , 2007, , .		9
106	Ultra-compact monolithically integrated photonic switches in InP. , 2007, , .		0
107	Development and fabrication of monolithically integrated optical packet switches. Journal of Optical Networking, 2007, 6, 157.	2.5	0
108	Optical system integration and reliability of very large arrays of individually addressable high-power single mode lasers. , 2006, 6133, 71.		0

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109	1.3 Âµm single-mode extended cavity GaInNAs lasers produced using a sputtered SiO2 quantum well intermixing technique. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 399-402.	0.8	0
110	The role of monolithic integration in advanced laser products. Journal of Crystal Growth, 2006, 288, 2-6.	0.7	9
111	Spatially resolved photoluminescence and Raman spectroscopy of bandgap gratings fabricated in GaAs/AlAs superlattice waveguide using quantum well intermixing. Journal of Crystal Growth, 2006, 288, 53-56.	0.7	4
112	Monolithically Integrated Optical Packet Switches for High-Speed LANs. , 2006, , .		0
113	Band gap gratings using quantum well intermixing for quasi-phase-matching. Journal of Applied Physics, 2006, 100, 123107.	1.1	6
114	Novel High-Brightness Laser Dtodes at 830 nm. , 2006, , .		2
115	Passive modelocking of InGaAsPâˆ•InP laser diode over wide operating temperature range. Electronics Letters, 2005, 41, 1380.	0.5	1
116	Influence of operating temperature on passive mode locking of InGaAsP/InP laser diode. , 2005, , .		0
117	Design and fabrication of low beam divergence and high kink-free power lasers. IEEE Journal of Quantum Electronics, 2005, 41, 1124-1130.	1.0	62
118	Monolithically integrated InGaAs-AlGaInAs Mach-Zehnder Interferometer optical switch using quantum-well intermixing. IEEE Photonics Technology Letters, 2005, 17, 783-785.	1.3	24
119	Current injection tunable monolithically integrated InGaAs-InAlGaAs asymmetric Mach-Zehnder interferometer using quantum-well intermixing. IEEE Photonics Technology Letters, 2005, 17, 1677-1679.	1.3	5
120	Very large arrays of individually addressable high-power single-mode laser arrays in the 800- to 1000-nm wavelength range obtained by quantum well intermixing techniques. , 2005, , .		6
121	Benefits of quantum well intermixing in high power diode lasers. , 2004, 5365, 1.		4
122	The Definition of Multiple Bandgaps in Quantum-Dot Material by Intermixing. Materials Research Society Symposia Proceedings, 2004, 829, 114.	0.1	2
123	Self-focused distributed Bragg reflector laser diodes. Journal of Applied Physics, 2004, 95, 1502-1509.	1.1	12
124	Passive Mode Locking of InAlGaAs 1.3->tex<$muhboxm$>/tex<Strained Quantum Wells Extended Cavity Laser Fabricated by Quantum-Well Intermixing. IEEE Photonics Technology Letters, 2004, 16, 374-376.	1.3	11
125	BEAM: design and characterization of a 10-Gb/s broadband electroabsorption modulator. , 2004, , .		0
126	Selective modification of the band gaps of GaInNas/GaAs structures by quantum well intermixing techniques. Materials Science and Engineering C, 2003, 23, 983-987.	3.8	2

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127	Dynamic modal analysis of monolithic mode-locked semiconductor lasers. IEEE Journal of Selected Topics in Quantum Electronics, 2003, 9, 844-856.	1.9	18
128	Characterization of selective quantum well intermixing in 1.3 Î¼m GaInNAs/GaAs structures. Journal of Applied Physics, 2003, 94, 1550-1556.	1.1	21
129	Selective modification of band gap in GaInNAs/GaAs structures by quantum-well intermixing. Applied Physics Letters, 2003, 82, 4259-4261.	1.5	10
130	Quantum well intermixing in GaInNAs/GaAs structures. Journal of Applied Physics, 2003, 94, 7581.	1.1	19
131	Electron-beam writing of photonic crystal patterns using a large beam-spot diameter. Nanotechnology, 2003, 14, 1004-1008.	1.3	9
132	Optoelectronics education training programs in Scotland. , 2002, 4588, 326.		0
133	<title>Self-focused distributed Bragg reflector QW laser diodes</title>. , 2002, , .		0
134	Efficient direct locking of colliding pulse mode-locked lasers on semi-insulating substrate at 1.5 Î¼m. IEEE Photonics Technology Letters, 2002, 14, 1049-1051.	1.3	13
135	High brightness single-mode ridge laser utilizing buried heterostructure defined by quantum-well intermixing. IEEE Photonics Technology Letters, 2002, 14, 1391-1393.	1.3	10
136	Improved catastrophic optical damage level from laser with nonabsorbing mirrors. IEEE Photonics Technology Letters, 2002, 14, 1394-1396.	1.3	46
137	Ultrafast harmonic mode-locking of monolithic compound-cavity laser diodes incorporating photonic-bandgap reflectors. IEEE Journal of Quantum Electronics, 2002, 38, 1-11.	1.0	52
138	The effect of cladding layer thickness on large optical cavity 650-nm lasers. IEEE Journal of Quantum Electronics, 2002, 38, 285-290.	1.0	17
139	The application of supported gold catalysts to automotive pollution abatement. Catalysis Today, 2002, 72, 145-156.	2.2	66
140	3-D GaAs radiation detectors. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2002, 477, 198-203.	0.7	4
141	Monolithic fabrication of 2 /spl times/ 2 crosspoint switches in InGaAs-InAlGaAs multiple quantum wells using quantum-well intermixing. IEEE Photonics Technology Letters, 2001, 13, 1292-1294.	1.3	37
142	<title>Ultrafast harmonic mode-locking of monolithic compound-cavity laser diodes incorporating photonic-bandgap reflectors</title>. , 2001, , .		4
143	<title>Hybrid mode-locking of a monolithic semiconductor laser on semi-insulating InP substrate</title>. , 2001, 4598, 157.		0
144	<title>Progress in quantum dots for optoelectronics applications</title>. , 2001, 4598, 106.		3

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145	Patterned dielectric mirrors for lateral overgrowth of GaN-based lasers.. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 82, 245-247.	1.7	9
146	Buried Dielectric Mirrors for the Lateral Overgrowth of GaN-Based Microcavities. Physica Status Solidi A, 2001, 183, 145-149.	1.7	5
147	Controlled intermixing in InGaAsP multiquantum wells by plasma immersion ion implantation of argon. Nuclear Instruments & Methods in Physics Research B, 2001, 173, 304-310.	0.6	1
148	<title>Ultrafast all-optical switching and demultiplexing using intersubband transitions in InGaAs/AlAsSb quantum well structures</title>. , 2001, , .		4
149	Optical loss in large optical cavity 650 nm lasers. Semiconductor Science and Technology, 2001, 16, L72-L75.	1.0	1
150	Terahertz repetition frequencies from harmonic mode-locked monolithic compound-cavity laser diodes. Applied Physics Letters, 2001, 78, 3571-3573.	1.5	19
151	Demonstration of passive Q-switching in multiquantum well InGaAs/AlGaInAs diode laser. Electronics Letters, 2000, 36, 952.	0.5	3
152	High-power and high-brightness visible semiconductor laser diodes. , 2000, 3947, 91.		0
153	Multi-gigabit WDM optical networking for next generation avionics system communications. Optics and Lasers in Engineering, 2000, 33, 277-297.	2.0	2
154	Engineering quantum-dot lasers. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 8, 154-163.	1.3	26
155	Monolithically integrated distributed Bragg reflector lasers for 1.5 Î¼m operation with band gap shifted grating section. Optical Materials, 2000, 14, 193-196.	1.7	1
156	Monolithic and multi-GigaHertz mode-locked semiconductor lasers: Constructions, experiments, models and applications. IEE Proceedings: Optoelectronics, 2000, 147, 251-278.	0.8	233
157	Semiconductor photonic integration: a regrowth free approach. , 2000, , .		0
158	Multi-wavelength lasers fabricated by an Al layer controlled quantum well intermixing technology. Journal of Applied Physics, 2000, 88, 3458-3462.	1.1	8
159	High-spatial-resolution quantum-well intermixing process in GaInAs/GaInAsP laser structure using pulsed-photoabsorption-induced disordering. Journal of Applied Physics, 2000, 87, 2775-2779.	1.1	16
160	Control of the band-gap shift in quantum-well intermixing using a germanium interlayer. Applied Physics Letters, 2000, 76, 1582-1584.	1.5	9
161	GaAs/AlGaAs waveguide pin photodiodes with non-absorbing input facets fabricated by quantum well intermixing. Electronics Letters, 2000, 36, 749.	0.5	7
162	Passive harmonic modelocking in monolithic compound-cavity laser diodes. Electronics Letters, 2000, 36, 1930.	0.5	2

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163	Quasi phase matching in GaAsâ€“AlAs superlattice waveguides through bandgap tuning by use of quantum-well intermixing. Optics Letters, 2000, 25, 1370.	1.7	68
164	Selective control of self-organized In[sub 0.5]Ga[sub 0.5]As/GaAs quantum dot properties: Quantum dot intermixing. Journal of Applied Physics, 2000, 88, 4619.	1.1	61
165	Fabrication of 2 x 2 crosspoint switches using a sputtered SiO2 intermixing technique. IEEE Photonics Technology Letters, 2000, 12, 287-289.	1.3	10
166	Control of multiple bandgap shifts in InGaAs-AlInGaAs multiple-quantum-well material using different thicknesses of PECVD SiO2 protection layers. IEEE Photonics Technology Letters, 2000, 12, 1141-1143.	1.3	21
167	Buffering Strategies for Optical Packet Switches. , 2000, , .		1
168	Control of silica cap properties by oxygen plasma treatment for single-cap selective impurity free vacancy disordering. Applied Physics Letters, 1999, 74, 732-734.	1.5	27
169	Extended Cavity Lasers in InGaAs-InGaAsP and GaInP-AlGaInP Multi-Quantum Well Structure Using a Sputtered SiO2Technique. Japanese Journal of Applied Physics, 1999, 38, 1246-1248.	0.8	12
170	Ultrafast two-photon absorption optical thresholding of spectrally coded pulses. Optics Communications, 1999, 167, 225-233.	1.0	13
171	Analysis of harmonic (sub)THz passive mode-locking in monolithic compound cavity Fabry-Perot and ring laser diodes. IEE Proceedings: Optoelectronics, 1999, 146, 55-61.	0.8	28
172	Dielectric Bragg Mirrors for InGaN Surface-Emitting Lasers. Physica Status Solidi A, 1999, 176, 67-71.	1.7	9
173	Spectral and dynamic properties of InAs-GaAs self-organized quantum-dot lasers. IEEE Journal of Selected Topics in Quantum Electronics, 1999, 5, 648-657.	1.9	45
174	Broad optical bandwidth InGaAs-InAlGaAs light-emitting diodes fabricated using a laser annealing process. IEEE Photonics Technology Letters, 1999, 11, 1557-1559.	1.3	16
175	Quantum Well Intermixing Using Sputtered Silica for Photonic Integrated Circuits Operating Around 1550 nm. Materials Research Society Symposia Proceedings, 1999, 607, 479.	0.1	0
176	Multiwavelength lasers fabricated by a novel impurity-free quantum-well intermixing technology. , 1999, , .		0
177	Decomposition and stability of group-III nitride ternary cubic spontaneously ordered alloys. IEEE Journal of Selected Topics in Quantum Electronics, 1998, 4, 531-536.	1.9	8
178	Low-temperature photoluminescence of heavy-ion-implanted InGaP solid solutions. Technical Physics Letters, 1998, 24, 690-691.	0.2	0
179	Passive modelocking in semiconductor lasers with monolithically integrated passive waveguides. IEE Proceedings: Optoelectronics, 1998, 145, 43-46.	0.8	6
180	Technology development of 3-D GaAs radiation detectors. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 1998, 410, 115-123.	0.7	3

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181	Monolithic integration via a universal damage enhanced quantum-well intermixing technique. IEEE Journal of Selected Topics in Quantum Electronics, 1998, 4, 636-646.	1.9	89
182	Quantitative model for the kinetics of compositional intermixing in GaAs-AlGaAs quantum-confined heterostructures. IEEE Journal of Selected Topics in Quantum Electronics, 1998, 4, 653-660.	1.9	6
183	A study of impurity-free vacancy disordering in GaAs-AlGaAs for improved modeling. IEEE Journal of Selected Topics in Quantum Electronics, 1998, 4, 661-668.	1.9	14
184	Modulation of the second-order nonlinear tensor components in multiple-quantum-well structures. IEEE Journal of Selected Topics in Quantum Electronics, 1998, 4, 695-700.	1.9	34
185	Introduction To The Issue On Interdiffused Quantum-well Materials And Devices. IEEE Journal of Selected Topics in Quantum Electronics, 1998, 4, 581-583.	1.9	12
186	Micromachined pattern transfer into CVD diamond. Diamond and Related Materials, 1998, 7, 1148-1154.	1.8	11
187	High-power antiguided laser array fabricated without the need for overgrowth. IEEE Photonics Technology Letters, 1998, 10, 328-330.	1.3	12
188	Monolithic integration in InGaAs-InGaAsP multiquantum-well structure using laser processing. IEEE Photonics Technology Letters, 1998, 10, 769-771.	1.3	23
189	Bandgap tuning of visible laser material. Electronics Letters, 1998, 34, 665.	0.5	6
190	Longitudinal mode grouping in InGaAs/GaAs/AlGaAs quantum dot lasers: Origin and means of control. Electronics Letters, 1998, 34, 2035.	0.5	39
191	Reduced damage reactive ion etching process for fabrication of InGaAsP/InGaAs multiple quantum well ridge waveguide lasers. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1998, 16, 1818.	1.6	4
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